



PMB045T045SS-255A

2A/45V⁽¹⁾, low VF Planar MOS barrier diode

Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	1142μm	45.0 mil
	Top Metal Pad Size (B)	1042 μm	41.0mil
	Chip Size (C)	/	/
	Wafer Thickness (D)	255 μm	10.0 mil
	Scribe Line Width (E)	80 μm	3.15 mil
	Wafer Size	6 inch	
	Top Side Metallization	PMB045T045SS-255A	Ag
	Back Side Metallization	Ti Ni Ag	
	Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23°C±3°C)	

Electrical Characteristics (T_J=25°C, unless otherwise specified) ⁽²⁾

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V _{BR}	Reverse Breakdown Voltage	46	52	-	V	I _R =300μA
		-	0.42	0.48	V	I _F =2A ⁽³⁾
I _R	Reverse Leakage Current	-	50	150	μA	V _R =45V
T _J , T _{STG}	Operating and Storage Temperature	-40°C to 150°C Max				

Note:

(1) The preliminary wafer datasheet only for reference;

(2) This characteristics assumes the dies are assembled in DO-201 packages. Actual performance may degrade when assembled.

YJ does not guarantee device performance after assembly;

(3) Pulse Width t_p = < 300μS, Duty Cycle <2%;